

What is claimed is:

1. A method of fabricating an IPS mode LCD, comprising:
forming a first electrode and a second electrode on a first substrate;
forming a passivation film on one of the first and second electrodes; and
performing an orientation treatment of the passivation film by irradiating an ion beam on the passivation film.
2. The method according to claim 1, further comprising:
forming a gate line and a data line on the first substrate; and
forming a thin film transistor at a crossing point of the gate line and the data line.
3. The method according to claim 1, wherein the first electrode and the second electrode are arranged in a stripe configuration.
4. The method according to claim 1, wherein the first electrode and the second electrode are arranged in a zigzag configuration.
5. The method according to claim 1, wherein the first electrode, the second electrode and the data line are arranged in a zigzag configuration.
6. The method according to claim 2, wherein the first electrode and the second electrode are arranged in a zigzag configuration, and the gate line is arranged in a stripe configuration.

7. The method according to claim 2, wherein the first electrode, the second electrode and the gate line are arranged in a zigzag configuration.
8. The method according to claims 4, wherein the zigzag configuration has at least one bent portion.
9. The method according to claim 2, wherein the thin film transistor includes a gate electrode, a source electrode and a drain electrode.
10. The method according to claim 1, wherein the first electrode is a pixel electrode and the second electrode is a common electrode.
11. The method according to claim 1, further comprising forming an insulating layer on the first electrode.
12. The method according to claim 1, wherein the passivation film includes one of an organic material and an inorganic material.
13. The method according to claim 1, further comprising:
 - forming a black matrix layer on a second substrate;
 - forming a color filter layer on the black matrix layer;
 - forming an overcoat layer on the color filter layer;
 - irradiating an ion beam on the overcoat layer to perform an orientation treatment of the overcoat layer; and
 - forming a liquid crystal layer between the first and second substrates.

14. The method according to claim 13, wherein the overcoat layer includes one of an organic material and an inorganic material.

15. A method of fabricating an IPS mode LCD, comprising:
forming a pixel electrode and a common electrode on a first substrate;
forming a passivation film on the pixel electrode and the common electrode; and
performing an orientation treatment of the passivation film by irradiating an ion beam on the passivation film;
forming a black matrix layer on a second substrate;
forming a color filter layer on the black matrix layer;
forming an overcoat layer on the color filter layer; and
performing an orientation treatment of the overcoat layer by irradiating an ion beam on the passivation film.

16. The method according to claim 15, further comprising forming a liquid crystal layer between the first and second substrates.

17. The method according to claim 16, wherein forming a liquid crystal layer includes injecting the liquid crystal into a space between the first and second substrates.

18. The method according to claim 16, wherein forming a liquid crystal layer includes dispensing a liquid crystal on at least one of the first and second substrates.

19. The method according to claim 15, wherein the passivation film and the overcoat layer include one of an organic material and an inorganic material.

20. The method according to claim 19, wherein the passivation film and the overcoat layer are formed of one of a photo-acryl, a BCB (benzo cyclobutene), and a silicon oxide (SiO_x) and a silicon nitride (SiN_x).

21. The method according to claim 15, wherein irradiating the ion beam comprising;
generating a plasma from an ion beam source;
forming an ion beam from the plasma;
accelerating the ion beam by applying an electric field to an ion beam acceleration medium; and
irradiating the ion beam on one of the first and second substrates at a predetermined angle.

22. A method of fabricating an IPS mode LCD comprising:
forming an upper and lower substrate, the lower substrate having a common electrode and a pixel electrode;
cleaning the upper and lower substrates to remove foreign substances;
irradiating an ion beam on the upper and lower substrates for an orientation treatment;
forming a seal pattern at an edge portion of the upper substrate;
forming a spacer on the lower substrate;
attaching the upper substrate a predetermined distance from the lower substrate; and
forming a liquid crystal layer between the attached upper substrate and lower substrate.

23. The method of claim 22, wherein forming a liquid crystal layer includes dispensing a liquid crystal on at least one of the upper and lower substrates.

24. The method of claim 22, wherein forming a liquid crystal layer includes injecting a liquid crystal between the upper and lower substrates.